a high concentration source region of a second conductive type disposed in the semiconductor substrate and at one end of said gate electrode;

a low concentration drain region of the second conductive type disposed in the semiconductor substrate and provided to face said source region through a channel region;

a high concentration drain region of the second conductive type spaced away from another end of said gate electrode and disposed in said low concentration drain region; and

a middle concentration layer of the second conductive type disposed in said low concentration drain region and disposed at least from a predetermined position spaced away from said gate electrode to said high concentration drain region,

wherein an impurity concentration of said middle concentration layer increases from near the gate electrode to near said high concentration drain region.

2. (Amended) A semiconductor device according to claim 1, wherein said middle concentration layer is formed so that the impurity concentration gradually increases from said gate electrode to said high concentration drain region.

3. (Amended) A semiconductor device according to claim 1, wherein said middle concentration layer is formed so that the impurity concentration increases step by step from said gate electrode to said high concentration drain region.

4. (Amended) A semiconductor device according to claim 1, wherein said high concentration source region is formed in said low concentration source region.

5. (Amended) A semiconductor device according to Claim 4,

wherein said middle concentration layer is formed at an entire region spanning from said gate electrode to said high concentration drain region.

6. (Amended) A semiconductor device according to Claim 1,

wherein said middle concentration layer is formed at an entire region spanning from said gate electrode to said high concentration source·drain region. --